App. No. 10/708,618
Amendment dated August 12, 2005
Reply to Office action of April 18, 2005

Amendments to the Specification (other than claims):

Please replace paragraph [0038] with the following amended paragraph:

[0038] The Q factor and electric field pattern (radiation pattern) for a cavity made from a donor-type point defect 4 as is illustrated in Fig. 1 were simulated by the FDTD method. The simulation parameters were configured by selecting silicon for the slab 1; and setting approximately [[1.55 □m]] 1.55 μm, which is generally used in optical communications, for the wavelength λ; [[0.42 □m]] 0.42 μm for the lattice constant a; 0.6a for the slab 1 thickness; and 0.29a for the predetermined sectional radius of the through-holes 2.

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